

# **NXP PMEG2020EPK barrier rectifier datasheet**

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Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small DFN1608D-2 (SOD1608) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

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# PMEG2020EPK

20 V, 2 A low VF MEGA Schottky barrier rectifier

10 February 2014

Product data sheet

## 1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small DFN1608D-2 (SOD1608) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

## 2. Features and benefits

- Average forward current:  $I_{F(AV)} \leq 2$  A
- Reverse voltage:  $V_R \leq 20$  V
- Low forward voltage  $V_F \leq 450$  mV
- Low reverse current
- AEC-Q101 qualified
- Solderable side pads
- Package height typ. 0.37 mm
- Ultra small and leadless SMD plastic package

## 3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- LED backlight for mobile application
- Low power consumption applications
- Ultra high-speed switching
- Reverse polarity protection

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	average forward current	$\delta < 0.5$ ; $f = 20$ kHz; $T_{sp} \leq 130$ °C; square wave	-	-	2	A
		$\delta < 0.5$ ; $f = 20$ kHz; $T_{amb} \leq 65$ °C; square wave	[1]	-	2	A
$V_R$	reverse voltage	$T_j = 25$ °C	-	-	20	V
$V_F$	forward voltage	$I_F = 2$ A; pulsed; $t_p \leq 300$ $\mu$ s; $\delta \leq 0.02$ ; $T_j = 25$ °C	-	395	450	mV



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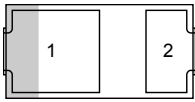



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_R$	reverse current	$V_R = 10\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	70	350	$\mu\text{A}$
<b>Dynamic characteristics</b>						
$t_{rr}$	reverse recovery time	$I_R = 0.5\text{ A}; I_F = 0.5\text{ A}; I_{R(\text{meas})} = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$	-	5	-	ns

[1] Device mounted on a ceramic Printed-Circuit Board (PCB),  $\text{Al}_2\text{O}_3$ , standard footprint.

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]	 <p>Transparent top view <b>DFN1608D-2 (SOD1608)</b></p>	 <p>sym001</p>
2	A	anode		

[1] The marking bar indicates the cathode.

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG2020EPK	DFN1608D-2	DFN1608D-2: leadless ultra small plastic package; 2 terminals	SOD1608

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG2020EPK	1110 0000

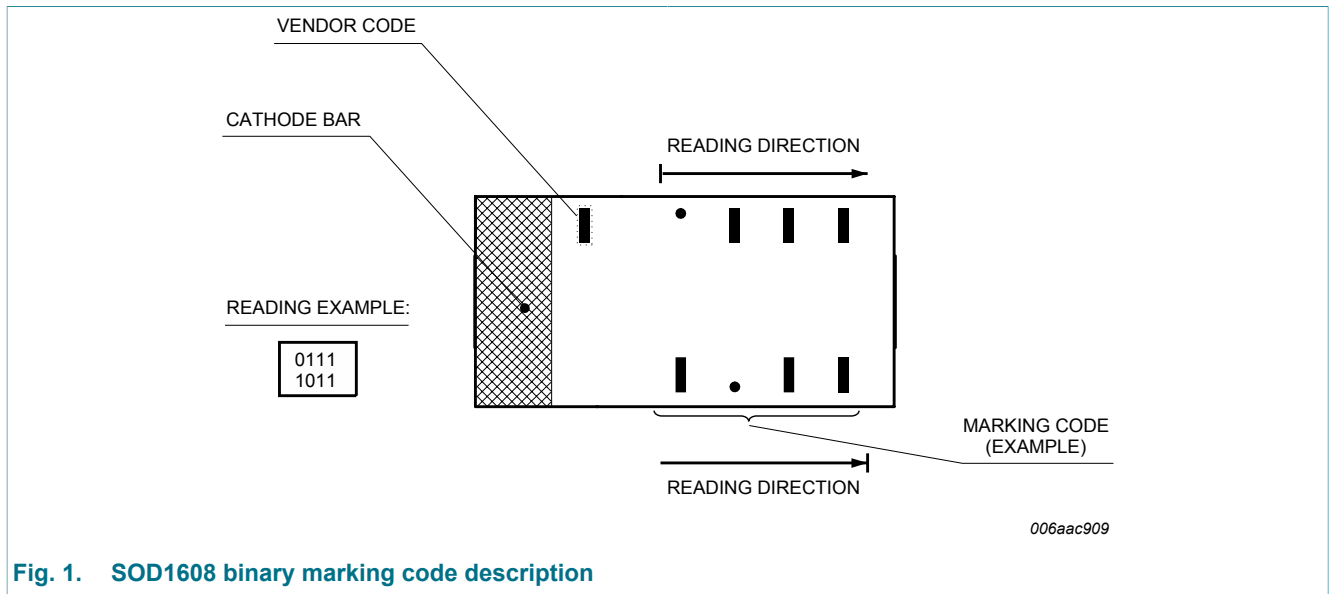


Fig. 1. SOD1608 binary marking code description

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_R$	reverse voltage	$T_j = 25\text{ °C}$		-	20	V
$I_F$	forward current	$T_{sp} \leq 125\text{ °C}$		-	2.83	A
$I_{F(AV)}$	average forward current	$\delta < 0.5$ ; $f = 20\text{ kHz}$ ; $T_{sp} \leq 130\text{ °C}$ ; square wave		-	2	A
		$\delta < 0.5$ ; $f = 20\text{ kHz}$ ; $T_{amb} \leq 65\text{ °C}$ ; square wave	[1]	-	2	A
$I_{FRM}$	repetitive peak forward current	$t_p = 1\text{ ms}$ ; $\delta = 0.25$		-	4	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 8\text{ ms}$ ; $T_{j(init)} = 25\text{ °C}$ ; square wave		-	5	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[2]	-	415	mW
			[3]	-	895	mW
			[1]	-	1565	mW
$T_j$	junction temperature			-	150	°C
$T_{amb}$	ambient temperature			-55	150	°C
$T_{stg}$	storage temperature			-65	150	°C

- [1] Device mounted on a ceramic Printed-Circuit Board (PCB),  $Al_2O_3$ , standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode  $1\text{ cm}^2$ .

## 9. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	-	300	K/W
			[1][3]	-	-	140	K/W
			[1][4]	-	-	80	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[5]	-	-	20	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses  $P_R$  are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode  $1\text{ cm}^2$ .
- [4] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.
- [5] Soldering point of cathode tab.

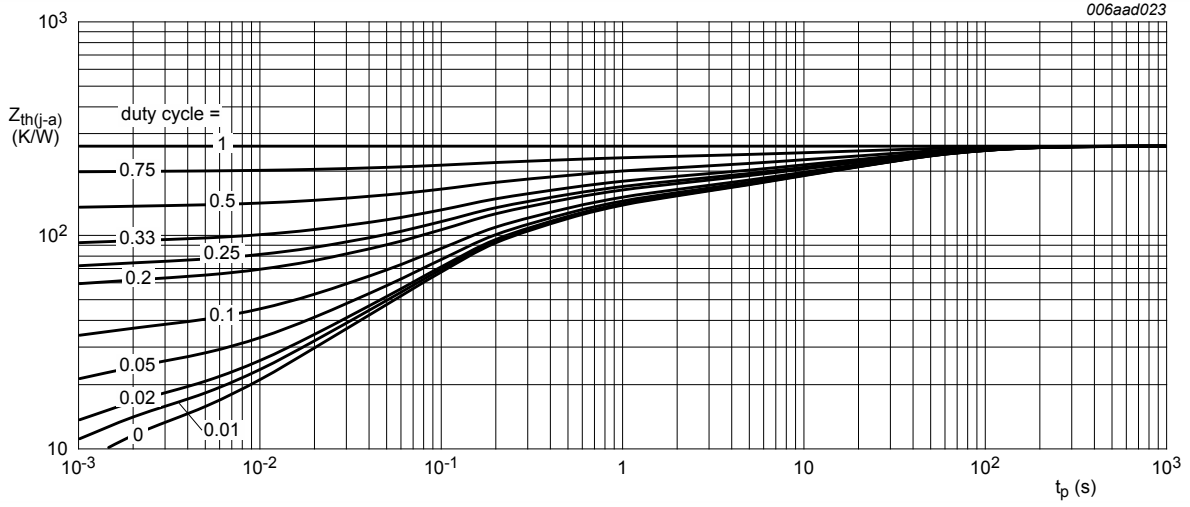


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

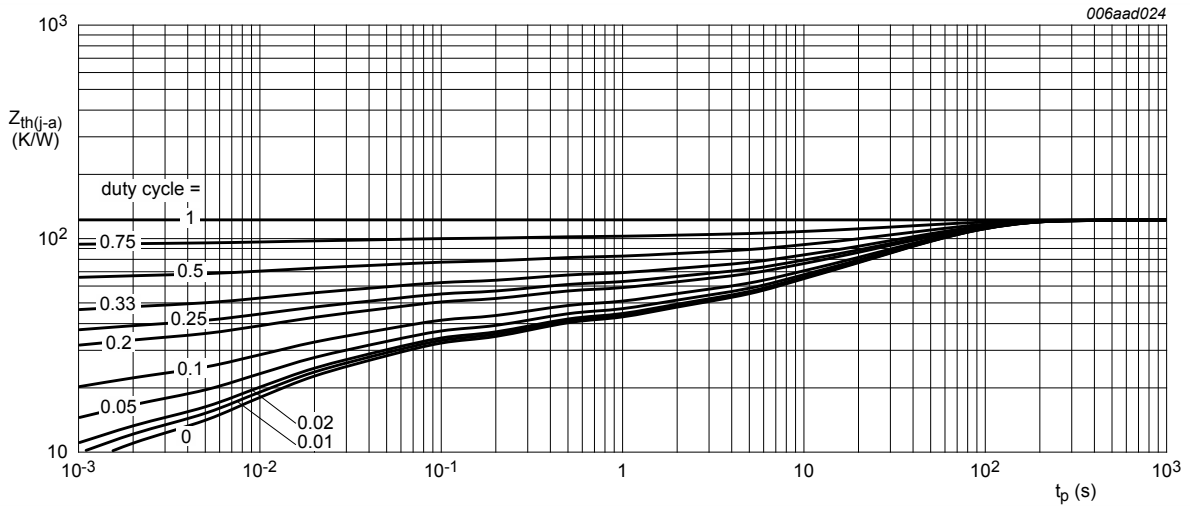
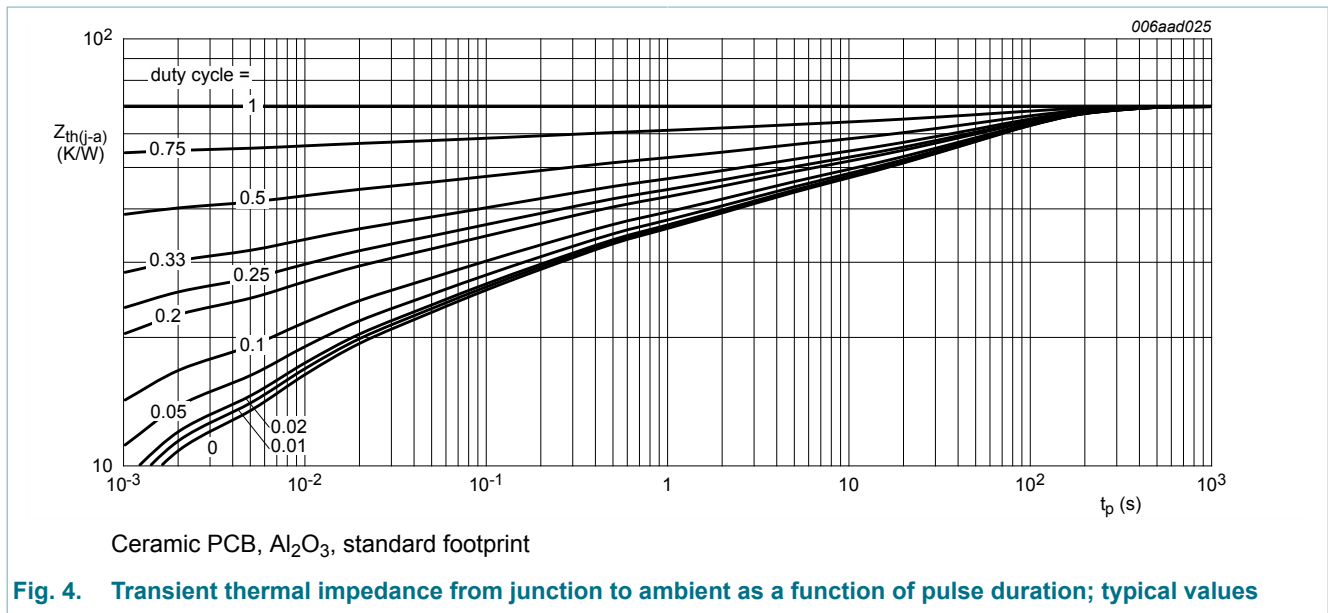


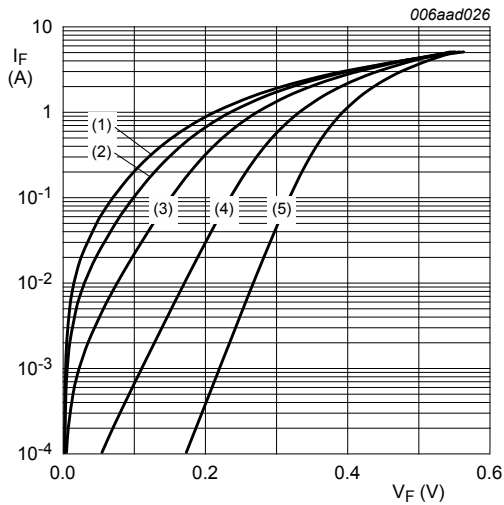
Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



## 10. Characteristics

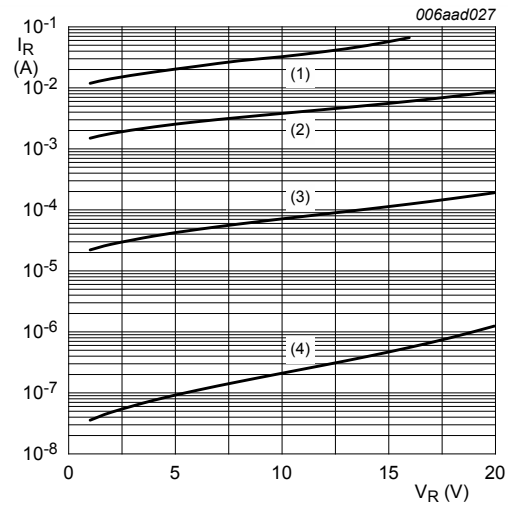
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	230	260	mV
		I <sub>F</sub> = 500 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	290	330	mV
		I <sub>F</sub> = 1 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	330	380	mV
		I <sub>F</sub> = 2 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	395	450	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C	-	70	350	μA
		V <sub>R</sub> = 20 V; T <sub>j</sub> = 25 °C	-	220	900	μA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	105	120	pF
		V <sub>R</sub> = 10 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	40	50	pF
<b>Dynamic characteristics</b>						
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 0.5 A; I <sub>R</sub> = 0.5 A; I <sub>R(meas)</sub> = 0.1 A; T <sub>j</sub> = 25 °C	-	5	-	ns
V <sub>FRM</sub>	peak forward recovery voltage	I <sub>F</sub> = 0.5 A; dI <sub>F</sub> /dt = 20 A/μs; T <sub>j</sub> = 25 °C	-	320	-	mV



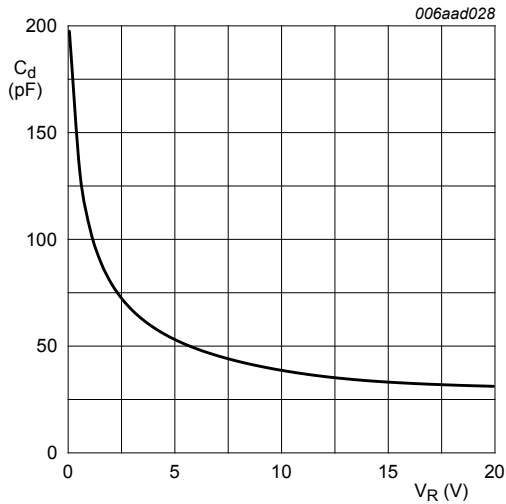
- (1)  $T_j = 150\text{ }^\circ\text{C}$
- (2)  $T_j = 125\text{ }^\circ\text{C}$
- (3)  $T_j = 85\text{ }^\circ\text{C}$
- (4)  $T_j = 25\text{ }^\circ\text{C}$
- (5)  $T_j = -40\text{ }^\circ\text{C}$

**Fig. 5. Forward current as a function of forward voltage; typical values**



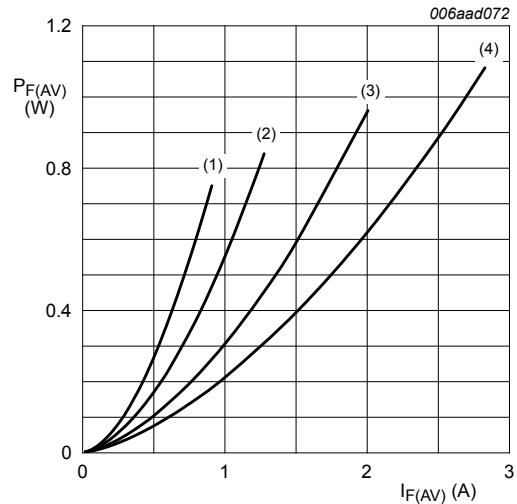
- (1)  $T_j = 125\text{ }^\circ\text{C}$
- (2)  $T_j = 85\text{ }^\circ\text{C}$
- (3)  $T_j = 25\text{ }^\circ\text{C}$
- (4)  $T_j = -40\text{ }^\circ\text{C}$

**Fig. 6. Reverse current as a function of reverse voltage; typical values**



$f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$

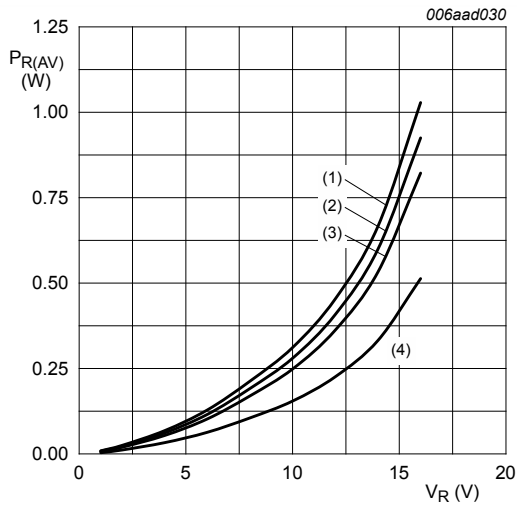
**Fig. 7. Diode capacitance as a function of reverse voltage; typical values**



- $T_j = 150\text{ }^\circ\text{C}$
- (1)  $\delta = 0.1$
- (2)  $\delta = 0.2$
- (3)  $\delta = 0.5$
- (4)  $\delta = 1$

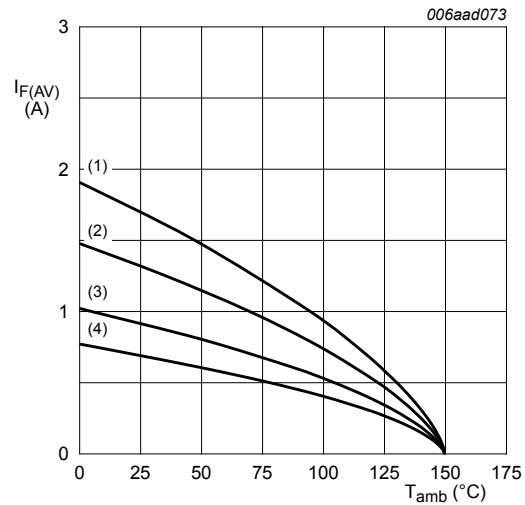
**Fig. 8. Average forward power dissipation as a function of average forward current; typical values**





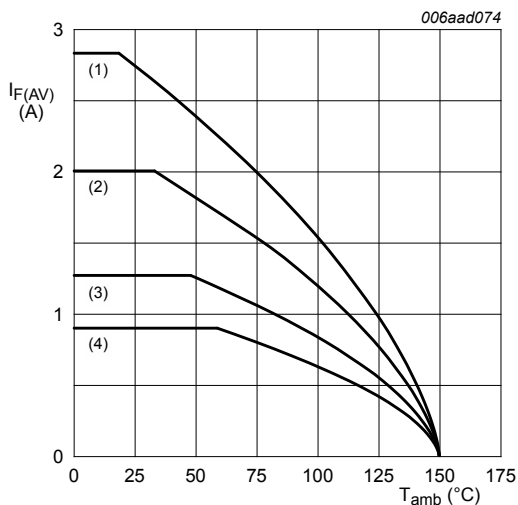
$T_j = 125\text{ }^\circ\text{C}$   
 (1)  $\delta = 1$   
 (2)  $\delta = 0.9$   
 (3)  $\delta = 0.8$   
 (4)  $\delta = 0.5$

**Fig. 9.** Average reverse power dissipation as a function of reverse voltage; typical values



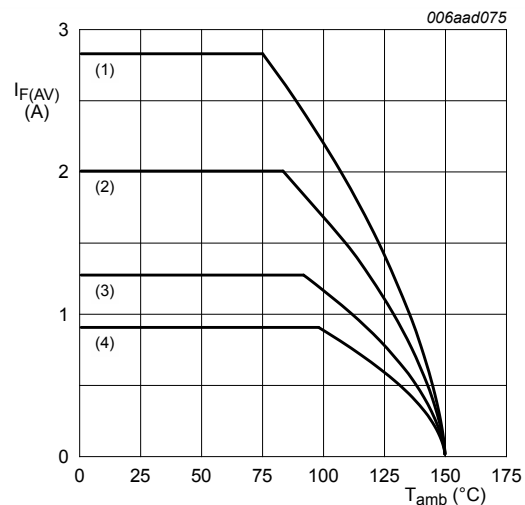
FR4 PCB, standard footprint  
 $T_j = 150\text{ }^\circ\text{C}$   
 (1)  $\delta = 1$  (DC)  
 (2)  $\delta = 0.5$ ;  $f = 20\text{ kHz}$   
 (3)  $\delta = 0.2$ ;  $f = 20\text{ kHz}$   
 (4)  $\delta = 0.1$ ;  $f = 20\text{ kHz}$

**Fig. 10.** Average forward current as a function of ambient temperature; typical values



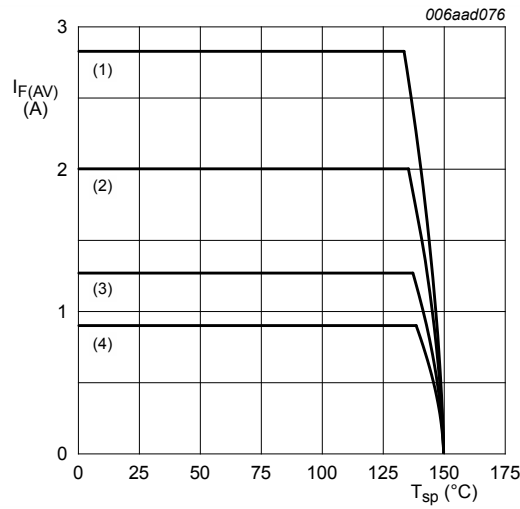
FR4 PCB, mounting pad for cathode  $1\text{ cm}^2$   
 $T_j = 150\text{ }^\circ\text{C}$   
 (1)  $\delta = 1$  (DC)  
 (2)  $\delta = 0.5$ ;  $f = 20\text{ kHz}$   
 (3)  $\delta = 0.2$ ;  $f = 20\text{ kHz}$   
 (4)  $\delta = 0.1$ ;  $f = 20\text{ kHz}$

**Fig. 11.** Average forward current as a function of ambient temperature; typical values



Ceramic PCB,  $\text{Al}_2\text{O}_3$ , standard footprint  
 $T_j = 150\text{ }^\circ\text{C}$   
 (1)  $\delta = 1$  (DC)  
 (2)  $\delta = 0.5$ ;  $f = 20\text{ kHz}$   
 (3)  $\delta = 0.2$ ;  $f = 20\text{ kHz}$   
 (4)  $\delta = 0.1$ ;  $f = 20\text{ kHz}$

**Fig. 12.** Average forward current as a function of ambient temperature; typical values



$T_j = 150\text{ °C}$

(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ;  $f = 20\text{ kHz}$

(3)  $\delta = 0.2$ ;  $f = 20\text{ kHz}$

(4)  $\delta = 0.1$ ;  $f = 20\text{ kHz}$

Fig. 13. Average forward current as a function of solder point temperature; typical values

### 11. Test information

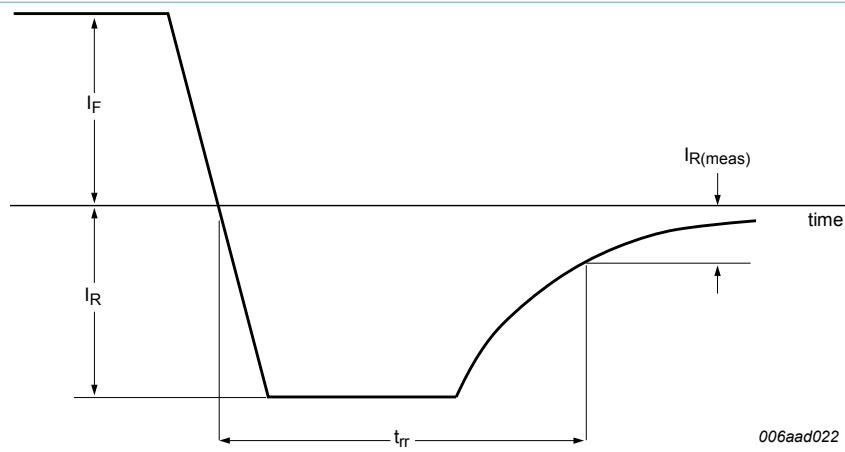


Fig. 14. Reverse recovery definition

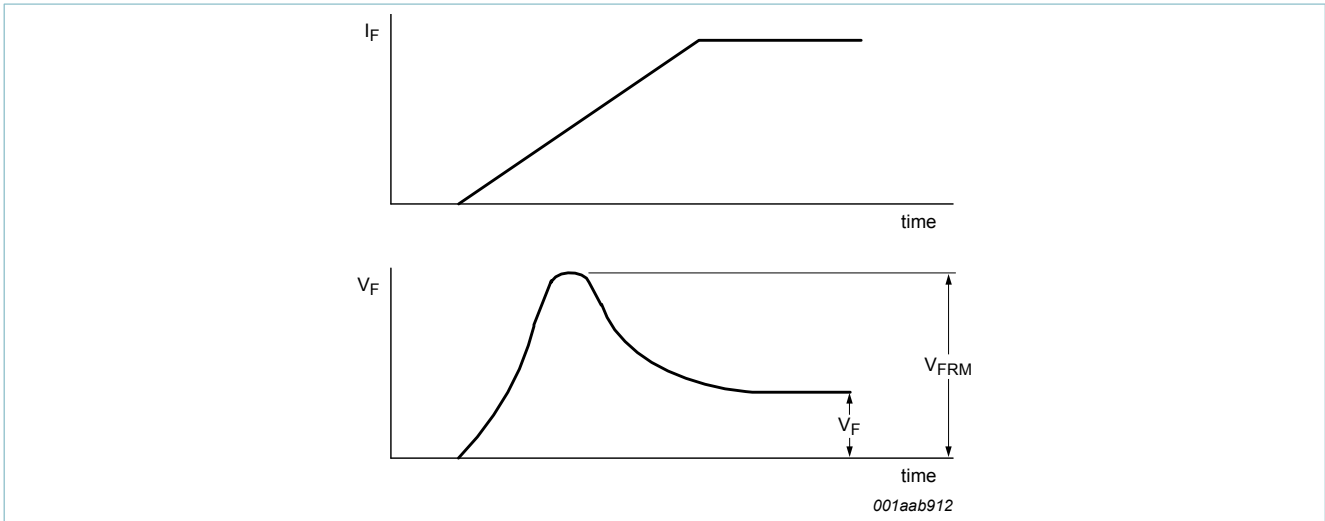


Fig. 15. Forward recovery definition

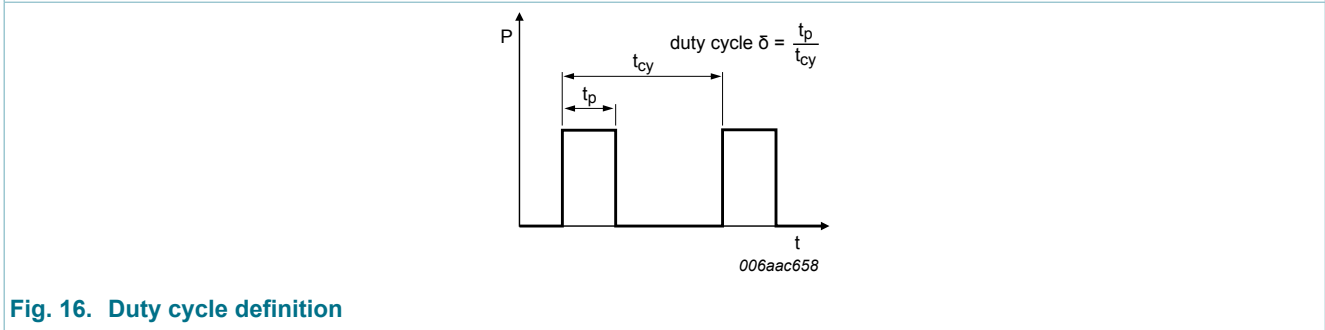


Fig. 16. Duty cycle definition

The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline

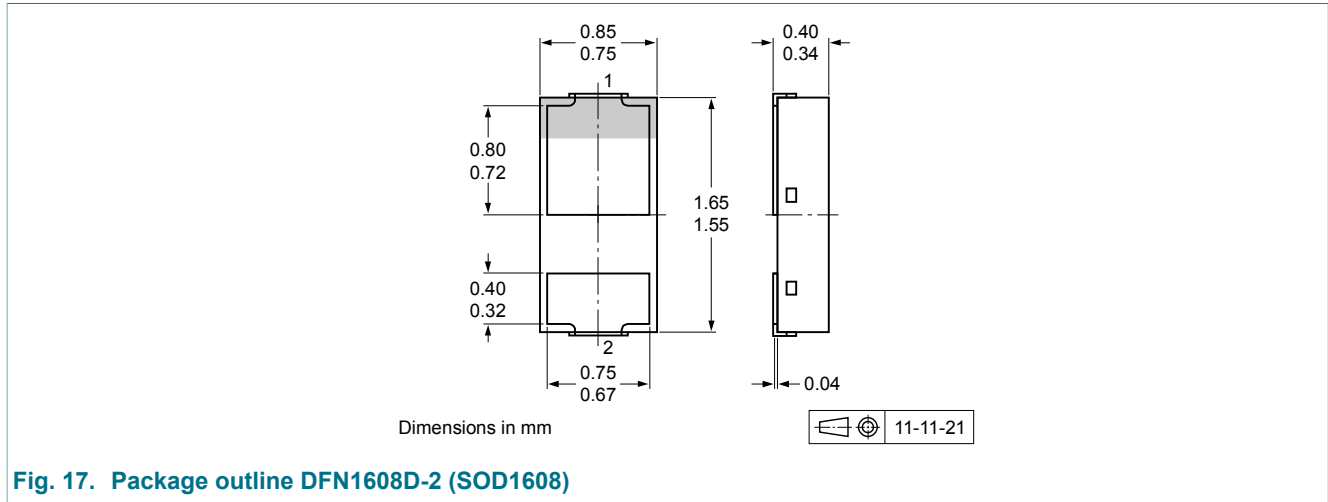


Fig. 17. Package outline DFN1608D-2 (SOD1608)

## 13. Soldering

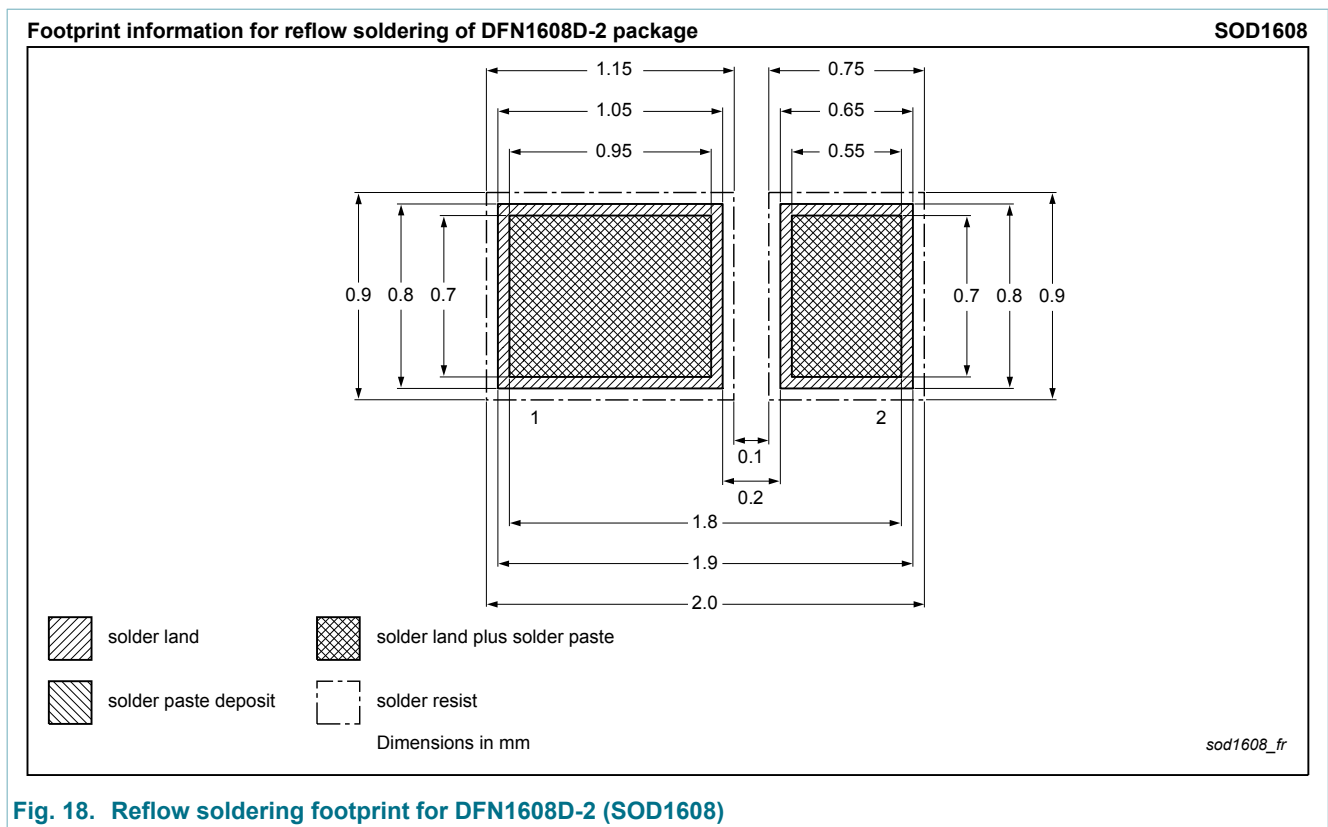


Fig. 18. Reflow soldering footprint for DFN1608D-2 (SOD1608)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG2020EPK v.2	20140210	Product data sheet	-	PMEG2020EPK v.1
Modifications:	Marking code corrected.			
PMEG2020EPK v.1	20120425	Product data sheet	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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 Date of release: 10 February 2014